
Dielectrics for Nanosystems 7: Materials Science, Processing, Reliability, and Manufacturing

Editors:

D. Misra

Y. Obeng

D. Bauza

T. Chikyow

Z. Chen

H. Iwai

K. Sundaram

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Published by

The Electrochemical Society

65 South Main Street, Building D
Pennington, NJ 08534-2839, USA

tel 609 737 1902

fax 609 737 2743

www.electrochem.org

ecstransactions™

Vol. 72, No. 2

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Published by:

The Electrochemical Society
65 South Main Street
Pennington, New Jersey 08534-2839, USA

Telephone 609.737.1902
Fax 609.737.2743
e-mail: ecs@electrochem.org
Web: www.electrochem.org

ISSN 1938-6737 (online)
ISSN 1938-5862 (print)
ISSN 2151-2051 (cd-rom)

ISBN 978-1-62332-354-7 (CD-ROM)
ISBN 978-1-60768-712-2 (PDF)

Printed in the United States of America.

ECS Transactions, Volume 72, Issue 2
Dielectrics for Nanosystems 7: Materials Science, Processing,
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